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L Number	Hits	Search Text	DB	Time stamp
1	89553	non-volatile or nonvolatile near5 memor\$3	USPAT;	2003/06/10 10:21
<b>'</b>	0,555	non-volutile of non-volutile nears memorus	US-PGPUB;	2003/00/10 10.21
			JPO	
2	18309	float\$3 near3 gate\$1	USPAT;	2003/06/10 10:22
-	10307	Tivatus ficats gateur	US-PGPUB;	2003/00/10 10.22
			логов,	
3	56191	control near2 gate\$1	USPAT;	2002/06/10 10:22
	30191	Control fical 2 gates i	US-PGPUB;	2003/06/10 10:22
			JPO	
4	25443	select\$3 near2 gate\$1	USPAT;	2002/06/10 10:22
*	23443	Sciecus fical 2 gales i	•	2003/06/10 10:22
			US-PGPUB; JPO	
5	95088	nolygiliaan or nolygi on nolygi on (nolygnytalling adi (gi on giliaan))		2002/06/10 10:22
	93088	polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon))	USPAT;	2003/06/10 10:23
			US-PGPUB;	
_	4202	(non-valatile on nonvalatile noors manages) and (floot\$2 man2 and \$1)	JPO	2002/06/10 10:02
6	4383	(non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1)	USPAT;	2003/06/10 10:23
		and (control near2 gate\$1) and (polysilicon or polysi or poly-si or	US-PGPUB;	
,	1754026	(polycrystalline adj (si or silicon))) source\$1 or drain\$1	JPO	2002/06/10 10 02
7	1754026	Source\$1 or drain\$1	USPAT;	2003/06/10 10:23
			US-PGPUB;	
8	4176	((non-realetile on non-realetile noonf noon-next) and (flootf2 noon2 not f1)	JPO	2002/06/10 10:24
°	4175	((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1)	USPAT;	2003/06/10 10:24
		and (control near2 gate\$1) and (polysilicon or polysi or poly-si or	US-PGPUB;	
9	201054	(polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)	JPO	2002/06/10 10:24
9	301054	etch\$3	USPAT;	2003/06/10 10:24
			US-PGPUB;	
10	132929	implant\$3	JPO	2002/06/10 10:24
10	132929	пиртанцээ	USPAT; US-PGPUB;	2003/06/10 10:24
			JPO	
11	1948	(((mon volotile on nonvolotile mont money) and (floot\$2 mon2	1	2003/06/10 10:24
11	1948	(((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3	USPAT;	2003/00/10 10:24
		gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and	US-PGPUB;	
		etch\$3 and implant\$3	ЈРО	
12	750	((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3	USPAT;	2003/06/10 10:26
12	/50	gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si	US-PGPUB;	2003/00/10 10.20
		or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and	ло ЛРО	
		etch\$3 and implant\$3) and (select\$3 near2 gate\$1)	110	
27	3543	eras\$3 near2 gate\$1	USPAT;	2003/06/10 12:16
2,	3543	Class Hoar Z gatcor	US-PGPUB;	2003/00/10 12:10
			JPO	
28	161024	polish\$3 or cmp	USPAT;	2003/06/10 12:17
	101024	polisius of emp	US-PGPUB;	2003/00/10 12.17
		•	JPO	
29	750	(((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3	USPAT;	2003/06/10 12:17
-		gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si	US-PGPUB;	2003/00/10 12:17
		or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and	JPO	
		etch\$3 and implant\$3) and (select\$3 near2 gate\$1)		
30	634	((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3	USPAT;	2003/06/10 12:17
		gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si	US-PGPUB;	
		or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and	JPO	
		etch\$3 and implant\$3) and (eras\$3 near2 gate\$1)		
31	309	(((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3	USPAT;	2003/06/10 12:17
		gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si	US-PGPUB;	
		or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and	JPO	
		etch\$3 and implant\$3) and (eras\$3 near2 gate\$1)) not (((((non-volatile		
		or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control		
		near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj	-	
		(si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3)		
		and (select\$3 near2 gate\$1))		

32	61	(polish\$3 or cmp) and ((((((non-volatile or nonvolatile near5 memor\$3)	USPAT;	2003/06/10 12:17
		and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or	US-PGPUB;	
1		polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or	JPO	
		drain\$1)) and etch\$3 and implant\$3) and (eras\$3 near2 gate\$1)) not		
		(((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3		
		gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si		
		or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and		
		etch\$3 and implant\$3) and (select\$3 near2 gate\$1)))		
33	248	((((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3	USPAT;	2003/06/10 12:22
		gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si	US-PGPUB;	
		or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and	JPO	
		etch\$3 and implant\$3) and (eras\$3 near2 gate\$1)) not (((((non-volatile		
		or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control		
	ļ	near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj		
		(si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3)		
		and (select\$3 near2 gate\$1))) not ((polish\$3 or cmp) and		
		((((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3		
		gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si		
		or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and		
		etch\$3 and implant\$3) and (eras\$3 near2 gate\$1)) not (((((non-volatile		
		or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control		
		near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj		
		(si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3)		
		and (select\$3 near2 gate\$1))))		